

# 30V N-Channel Power MOSFET



**SOT-23** 



#### Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

#### Note:

MSL 1 (Moisture Sensitivity Level) per J-STD-020

### **Key Parameter Performance**

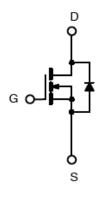
Parameter		Value	Unit	
$V_{DS}$		30	V	
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> = 10V	24	mΩ	
	V <sub>GS</sub> = 4.5V	34		
$Q_g$		4.1	nC	

### **Ordering Information**

Ordering code	Package	Packing		
TSM240N03CX RFG	SOT-23	3kpcs / 7" Reel		

Note: Halogen-free according to IEC 61249-2-21 definition

## **Block Diagram**



N-Channel MOSFET

#### **Absolute Maximum Ratings** (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	V	
Continuous Drain Current	$T_C = 25^{\circ}C$	· I <sub>D</sub>	6.5	А	
	T <sub>C</sub> = 100°C		4.1	Α	
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	26	Α	
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	32	mJ	
Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>D</sub>	1.56	W	
Operating Junction Temperature		TJ	150	°C	
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	80	°C/W

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**Electrical Specifications** (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
	$V_{GS} = 10V, I_D = 6A$	R <sub>DS(on)</sub>		17	24	mΩ
Drain-Source On-State Resistance	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4A			22	34	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1.2	1.4	2.5	V
	$V_{DS} = 30V, V_{GS} = 0V$				1	μΑ
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24V, T <sub>J</sub> = 125°C	I <sub>DSS</sub>			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	μΑ
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 4A$	g <sub>fs</sub>		6.5		S
Dynamic				L	•	I
Total Gate Charge (Note 3,4)		$Q_g$		4.1		
Gate-Source Charge (Note 3,4)	$V_{DS} = 15V, I_{D} = 6A,$	$Q_{gs}$		1		nC
Gate-Drain Charge (Note 3,4)	$V_{GS} = 4.5V$	$Q_{gd}$		2.1		
Input Capacitance		C <sub>iss</sub>		345		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		55		pF
Reverse Transfer Capacitance		$C_{rss}$		32		
Switching	-					I.
Turn-On Delay Time (Note 3,4)		t <sub>d(on)</sub>		2.8		
Turn-On Rise Time (Note 3,4)	$V_{DD} = 15V, I_{D} = 1A,$	t <sub>r</sub>		7.2		
Turn-Off Delay Time (Note 3,4)	$V_{GS} = 10V, R_G = 6\Omega$	t <sub>d(off)</sub>		15.8		ns
Turn-Off Fall Time (Note 3,4)		t <sub>f</sub>		4.6		1
Source-Drain Diode Ratings and Ch	aracteristic			L	•	I
Maximum Continuous Drain-Source		ı			6.5	۸
Diode Forward Current	Integral reverse diode in the MOSFET	I <sub>S</sub>			0.5	Α
Maximum Pulse Drain-Source Diode		I <sub>SM</sub>			26	Α
Forward Current						
Diode-Source Forward Voltage	$V_{GS} = 0V$ , $I_S = 1A$	$V_{SD}$			1	V

#### Note:

- 1. Pulse width limited by safe operating area
- 2. L = 1mH,  $I_{AS} = 8A$ ,  $V_{DD} = 25V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$
- 3. Pulse test: pulse width  $\leq$  300µs, duty cycle  $\leq$  2%
- 4. Switching time is essentially independent of operating temperature.

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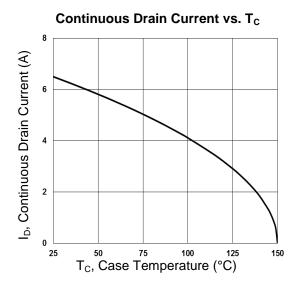


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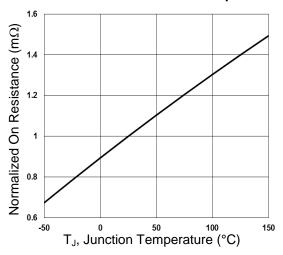
**Gate Charge** 



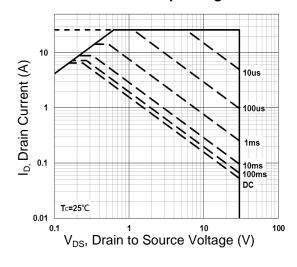
#### **Electrical Characteristics Curve**

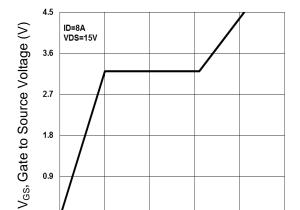


#### **On-Resistance vs. Junction Temperature**



#### **Maximum Safe Operating Area**



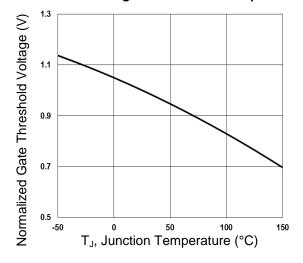


0.9

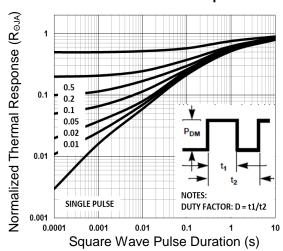
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#### Threshold Voltage vs. Junction Temperature

Qg, Gate Charge (nC)



#### **Normalized Thermal Transient Impedance Curve**



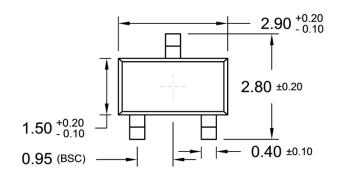
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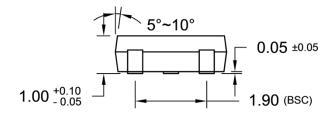


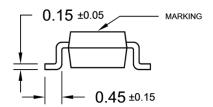
## 30V N-Channel Power MOSFET



## **SOT-23 Mechanical Drawing**

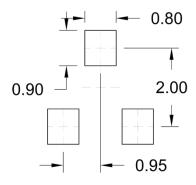






**Unit: Millimeters** 

## SUGGESTED PAD LAYOUT (Unit: Millimeters)



## **Marking Diagram**



24 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

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# Pb RóHS

# TSM240N03CX 30V N-Channel Power MOSFET

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